# Preventing Metallic Contamination in Image Sensors

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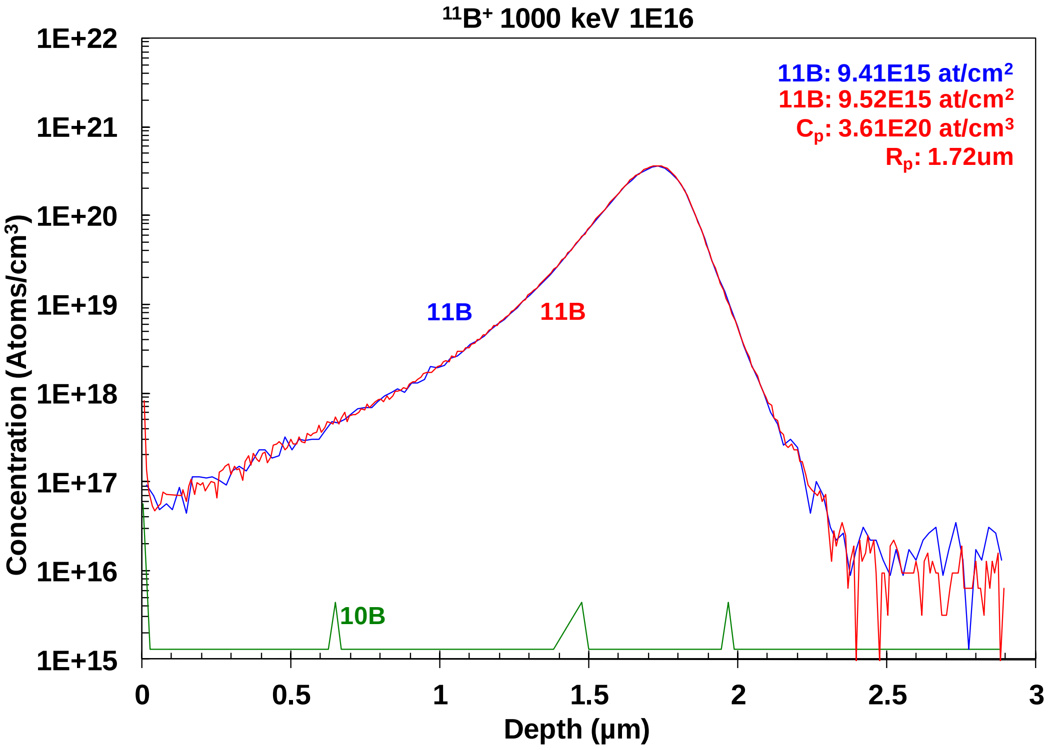
*generation current*

| Element | Trap Energy (eV above the Valence Band) |
|---|---|


11B+ 1000 keV 1E16
11B: 9.41E15 at/cm2
11B: 9.52E15 at/cm2
Cp: 3.61E20 at/cm3
Rp: 1.72um
11B
11B
10B
Concentration (Atoms/cm3)
1E+22
1E+21
1E+20
1E+19
1E+18
1E+17
1E+16
1E+15
0
0.5
1
1.5
2
2.5
3
Depth (µm)